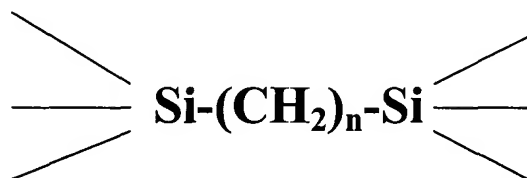


ABSTRACT OF THE DISCLOSURE

An organosilicon precursor for vapor deposition, e.g., low pressure (< 100 Torr), plasma-enhanced chemical vapor deposition (PECVD) of a low k, high strength dielectric film, wherein the precursor includes at least one of:

- (i) silicon-pendant oxiranyl functionality; and
- (ii) a disilyl moiety of the formula



wherein x is an integer having a value of from 0 to 4 inclusive. These precursors are useful for the formation of dielectric films having dielectric constants on the order of ~3 and less, and a hardness exceeding ~ 1 GigaPascals.